

TOSHIBA Bi-CMOS INTEGRATED CIRCUIT SILICON MONOLITHIC

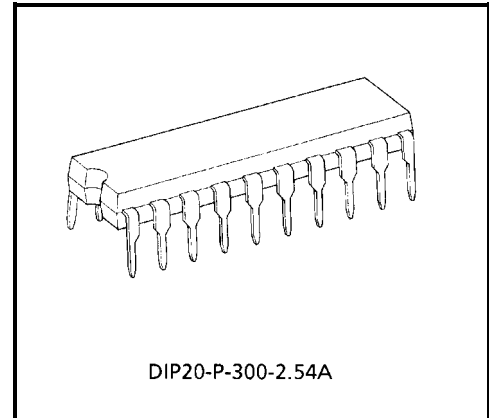
TD62C851P,TD62C852P

8BIT SERIAL-IN PARALLEL-OUT SHIFT REGISTER / LATCH DRIVERS

The TD62C851P and TD62C852P are monolithic circuits designed to be used together with Bi-CMOS integrated circuits. The devices consist of a 8bit shift register, 8bit latches, and 8 output circuits (integral clamp diodes for switching inductive loads).

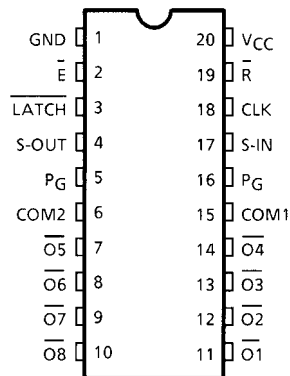
FEATURES

- 8bit serial-in parallel-out shift register / latch driver (Bi-CMOS process)
- Output sustaining voltage ; 50 V
- Output current ;
 TD62C851P 200 mA / ch (Low saturation type)
 TD62C852P 500 mA / ch (darlington type)
- Built-in output clamp diodes
- CMOS compatible inputs
- Package ; DIP20-P-300A

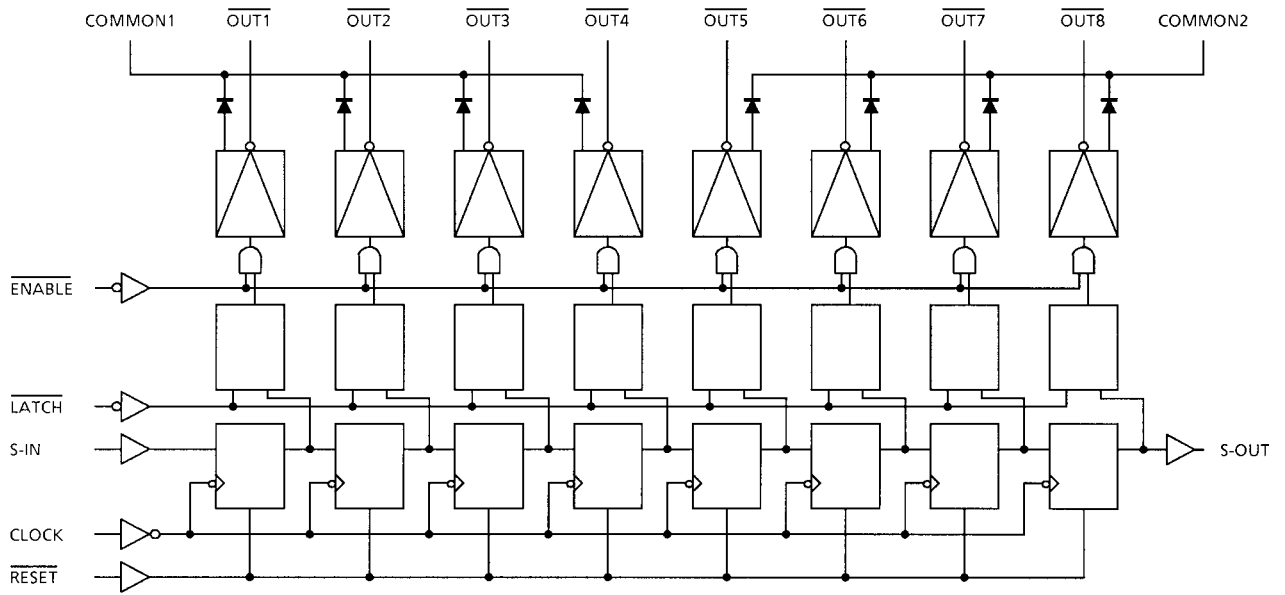


Weight: 2.25 g (Typ.)

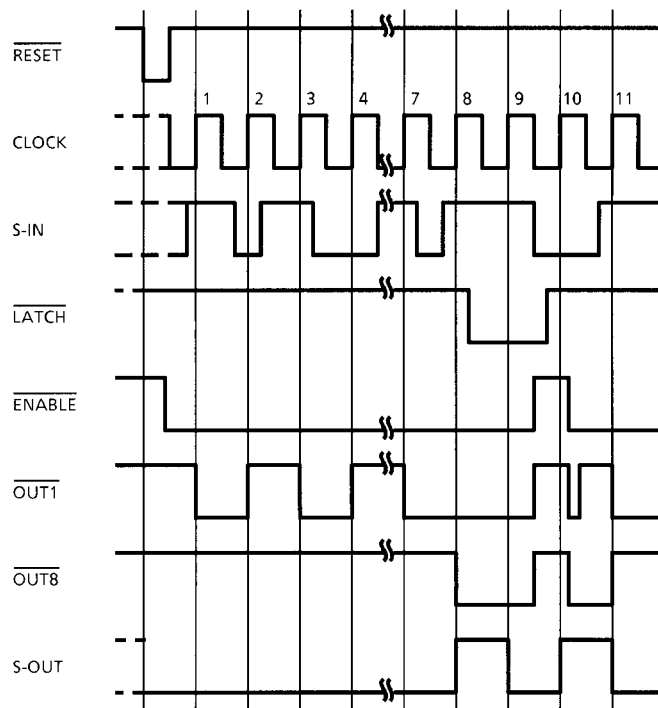
PIN CONNECTION (TOP VIEW)



BLOCK DIAGRAM

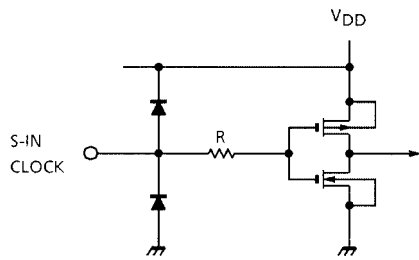


TIMING DIAGRAM

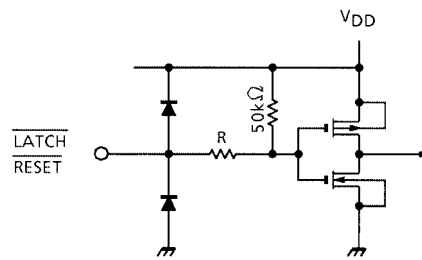


EQUIVALENT OF INPUTS AND OUTPUTS

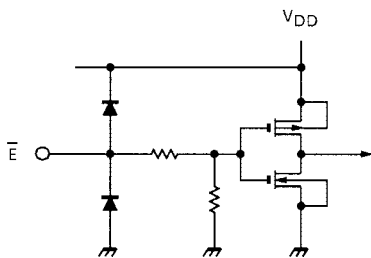
S-IN, clock terminal equivalent circuits



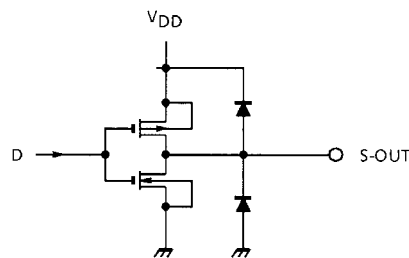
LATCH, RESET terminal equivalent circuits



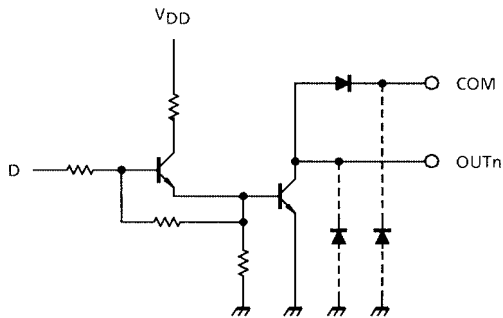
ENABLE terminal equivalent circuits



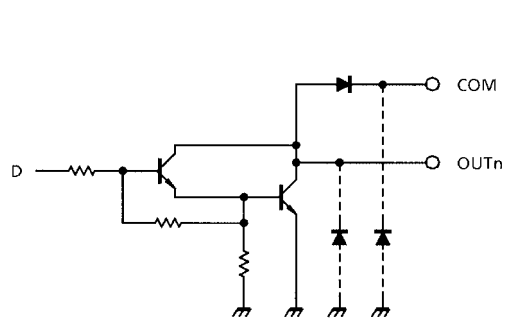
S-OUT terminal equivalent circuits



Output terminal equivalent circuits (TD62C851P)



Output terminal equivalent circuits (TD62C852P)



Note: The output parasitic diode cannot be used as clamp diode.

TRUTH TABLE

CK	\bar{E}	\bar{R}	$\overline{\text{LATCH}}$	S-IN	OUT		S-OUT
					$\bar{O}1$	$\bar{O}n-1$	
	L	H	H	L	OFF	$\bar{O}n-1$	Q ₇
	L	H	H	H	ON	$\bar{O}n-1$	Q ₇
	L	H	L	(*)	NC	NC	Q ₇
	H	H	(*)	(*)	OFF	NC	Q ₇
	(*)	(*)	(*)	(*)	NC	NC	Q ₇
(*)	(*)	L	H	(*)	OFF	OFF	L
(*)	H		L	(*)	NC	NC	L

CK = CLOCK
 E = ENABLE
 R = RESET
 LATCH = LATCH
 S-IN = SERIAL IN
 OUT = PARALLEL OUT
 S-OUT = SERIAL OUT

(*) = DON'T CARE
 NC = NO CHANGE
 L = LOW LEVEL
 H = HIGH LEVEL

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Supply Voltage	V _{DD}	-0.3~7.0	V
Output Sustaining Voltage	V _{CE (SUS)}	-0.5~50	V
Output Current	TD62C851P	200	mA / ch
	TD62C852P	500	
Input Voltage	V _{IN}	~0.4~V _{DD} + 0.3	V
Power Dissipation	P _D	1.47	W
Operating Temperature	T _{opr}	-40~85	°C
Storage Temperature	T _{stg}	-55~150	°C

RECOMMENDED OPERATING CONDITIONS (Ta = -40~85°C)

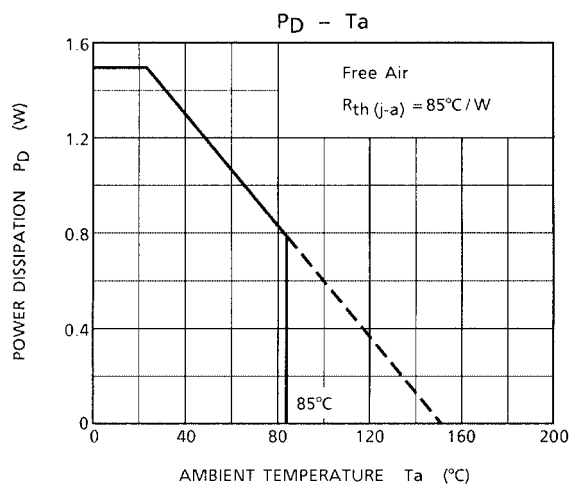
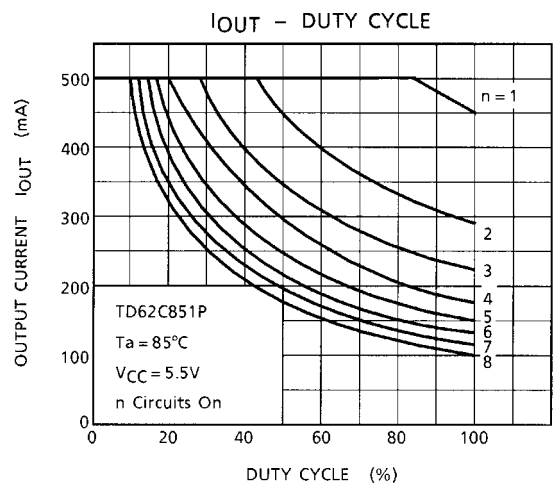
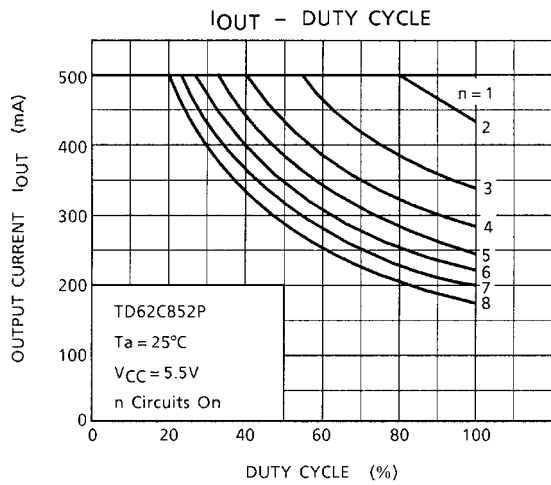
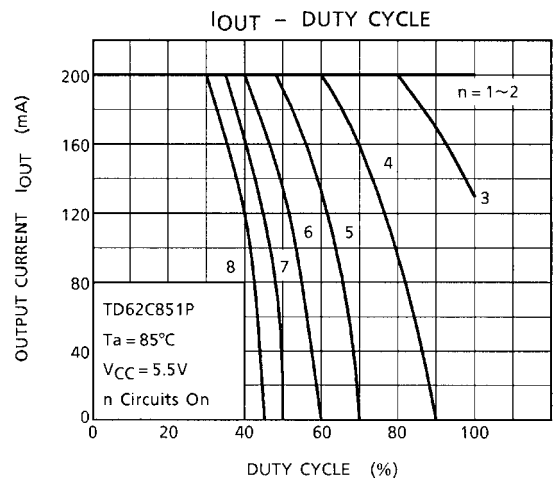
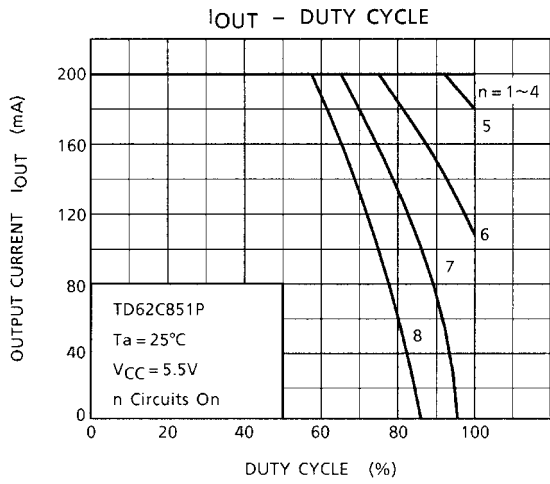
CHARACTERISTIC		SYMBOL	CONDITION	MIN	TYP.	MAX	UNIT	
Supply Voltage		V _{DD}	—	4.5	5.0	5.5	V	
Input Voltage		V _{IN}	—	0	—	V _{DD}	V	
Output Current ("H" Level)	S-OUT	I _{OH}	Ta = 25°C	—	—	-0.4	mA	
Output Voltage ("L" Level)	$\overline{O_n}$	V _{OH}	—	0	—	50	V	
Output Current ("L" Level)	S-OUT	I _{OL}	—	—	—	0.4	mA / ch	
			DC 1 circuit, Ta = 25°C	0	—	160		
	8 circuit on T _{pw} = 25 ms Ta = 85°C V _{DD} = 5.5 V		Duty = 10%	0	—	160		
			Duty = 40%	0	—	95		
	TD62C851P		$\overline{O_n}$	D C 1 circuit, Ta = 25°C	0	—		400
				8 circuit on T _{pw} = 25 ms Ta = 85°C V _{DD} = 5.5 V	Duty = 10%	0		—
Duty = 50%	0	—	170					
Clock Frequency		f _{CLOCK}	—	1.5	—	—	MHz	
Clock Pulse Width		f _w CLOCK	—	0.33	—	—	μs	
Data Set Up Time		t _{setup}	—	100	—	—	ns	
Data Hold Time		t _{hold}	—	100	—	—	ns	
Clamp Diode Reverse Voltage		V _R	—	0	—	50	V	
Clamp Diode Forward Current	TD62C851P	I _F	—	0	—	160	mA	
	TD62C852P		—	0	—	400		

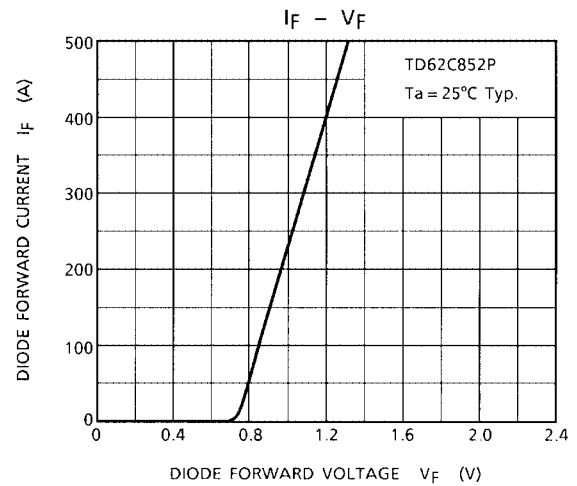
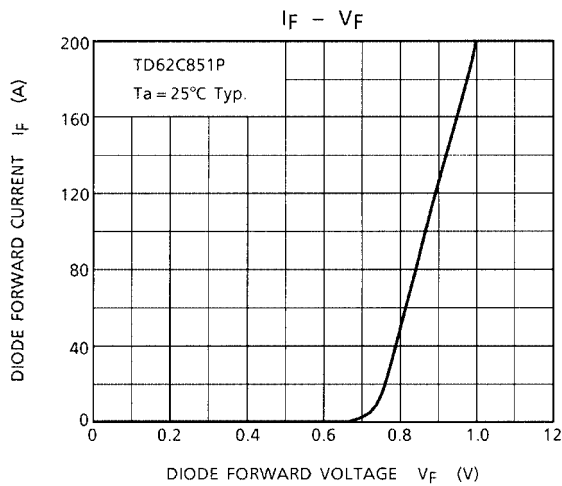
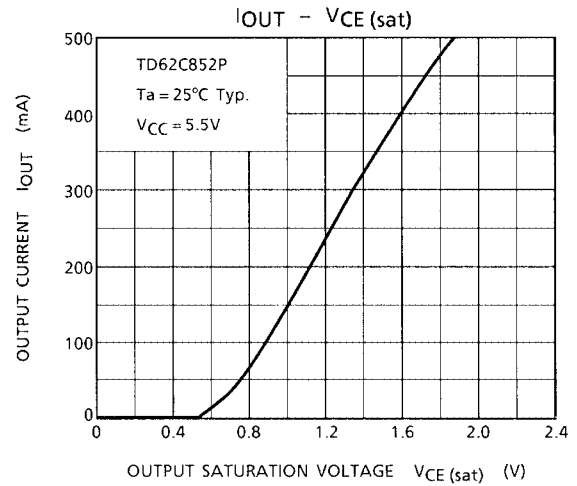
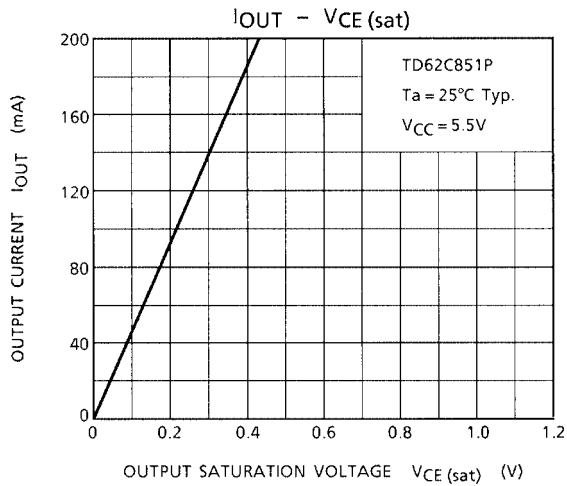
ELECTRICAL CHARACTERISTICS (Ta = -40~85°C)

CHARACTERISTIC		SYMBOL	TEST CIR-CUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT		
Input Voltage	"H" Level	V_{IH}	—	—	0.7 V_{DD}	—	—	V		
	"L" Level	V_{IL}	—	—	—	—	0.3 V_{DD}	V		
Input Current	"H" Level	I_{IH}	—	ENABLE, $V_{DD} = 5.5\text{ V}$ $V_{IH} = V_{DD}$	28	55	110	μA		
	"L" Level	I_{IL}	—	LATCH, RESET $V_{DD} = 5.5\text{ V}$, $V_{IL} = \text{GND}$	-55	-110	-275			
		I_{IN}	—	CLOCK, S-IN $V_{IN} = V_{CC}$ or GND	—	—	± 1.0			
Output Voltage	"H" Level	S-OUT	V_{OH}	—	$V_{DD} = 4.5\text{ V}$ $I_{OH} = -10\ \mu\text{A}$	3.9	4.1	—	V	
	"L" Level	S-OUT	V_{OL}	—	$V_{DD} = 4.5\text{ V}$	$I_{OL} = 0.8\text{ mA}$	—	0.2	0.4	V
		$\overline{\text{On}}$				$I_{OL} = 100\text{ mA}$	—	0.29	0.50	
						$I_{OL} = 160\text{ mA}$	—	0.39	0.65	
						$I_{OL} = 250\text{ mA}$	—	1.24	1.90	
$I_{OL} = 400\text{ mA}$	—	1.54	2.30							
Output Current	"H" Level	$\overline{\text{On}}$	I_{OH}	—	$V_{DD} = 5.5\text{ V}$, $V_{OH} = 50.0\text{ V}$	—	—	100	μA	
Operating Supply Current			I_{DD1}	—	$V_{DD} = 5.5\text{ V}$ $T_a = 25^\circ\text{C}$	ENABLE = "H"	—	130	200	mA
			I_{DD2}			$f_{CLK} = 1\text{ MHz}$ Output open DATA = 1 / 2 f_{CLK}	—	2.0	5.0	
		TD62C851P	I_{DD3}			1 circuit on $f_{CLK} = 1\text{ MHz}$ ENABLE = "L"	—	35	40	
		TD62C852P				—	1.0	1.5		
Clamp Diode Reverse Current			I_R	—	$V_R = 50\text{ V}$	—	—	50	μA	
Clamp Diode Forward Voltage		TD62C851P	V_F	—	$I_F = 160\text{ mA}$	—	1.0	2.0	V	
		TD62C852P			$I_F = 400\text{ mA}$	—	1.5	2.0		

SWITCHING CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Propagation Delay Time	Low-to-High	CK-S-OUT	t_{pLH}	$V_{DD} = 5.0\text{ V}, V_{IH} = 5.0\text{ V}$ $V_{IL} = 0\text{ V}, \text{Duty} = 50\%$ $R_L = \begin{cases} 300\ \Omega \text{ (TD62C851P)} \\ 120\ \Omega \text{ (TD62C852P)} \end{cases}$	—	0.40	0.65	μs
		$\overline{\text{CK}}-\overline{\text{On}}$			—	1.80	3.00	
		$\overline{\text{L}}-\overline{\text{On}}$			—	2.10	3.50	
		$\overline{\text{R}}-\overline{\text{On}}$			—	1.50	2.50	
		$\overline{\text{E}}-\overline{\text{On}}$			—	1.50	2.50	
	High-to-Low	CK-S-OUT	t_{pHL}		—	0.33	0.55	
		$\overline{\text{CK}}-\overline{\text{On}}$			—	0.41	0.70	
		$\overline{\text{L}}-\overline{\text{On}}$			—	0.30	0.50	
		R-S-OUT			—	0.25	0.42	
		$\overline{\text{E}}-\overline{\text{On}}$			—	0.21	0.35	
Maximum Clock Frequency		f_{MAX}	—	1.5	2.0	—	MHz	
Minimum Pulse Width	CLOCK	t_{wCK}	—	—	250	330	ns	
	$\overline{\text{LATCH}}$	t_{wL}	—	—	116	160		
	$\overline{\text{RESET}}$	t_{wR}	—	—	107	140		
Data Set Up Time		t_{setup}	—	—	30	60	ns	
Data Hold Time		t_{hold}	—	—	14	40		
Maximum Clock Rise Time		t_r	—	—	70	—	ns	
Maximum Clock Fall Time		t_f	—	—	70	—		





PRECAUTIONS FOR USING

This IC does not integrate protection circuits such as overcurrent and overvoltage protectors.

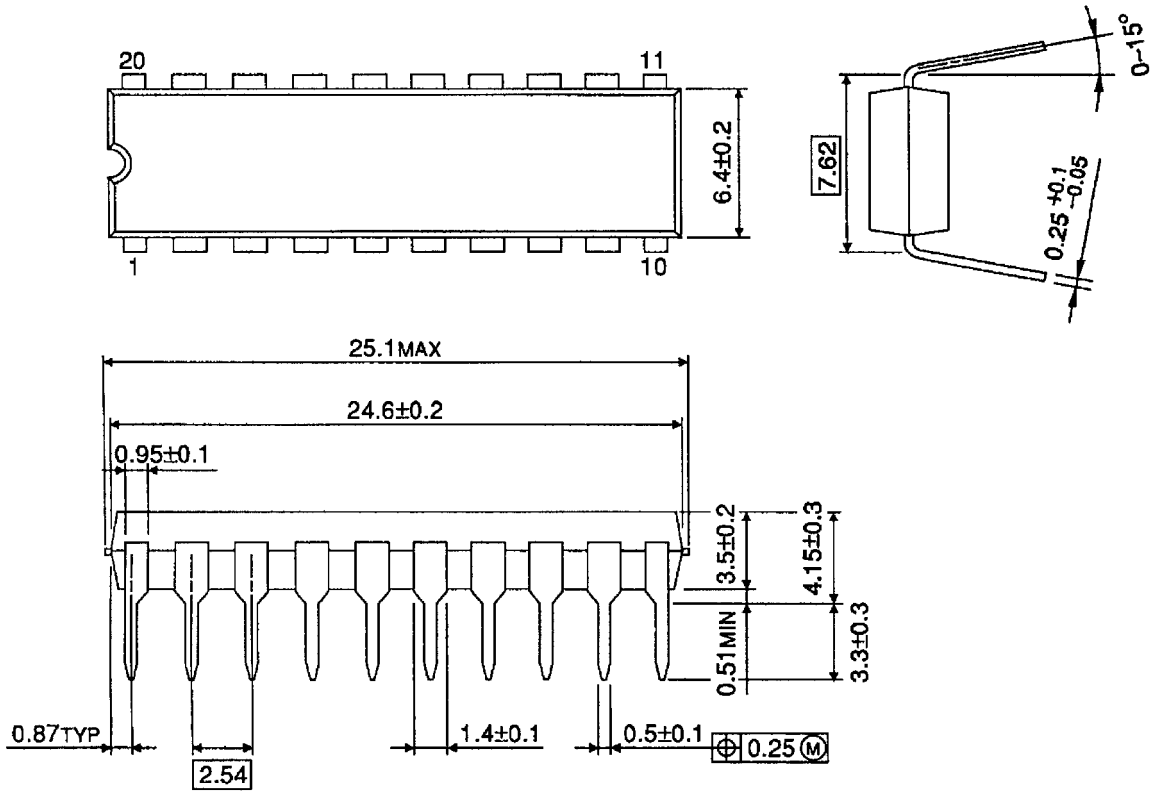
Thus, if excess current or voltage is applied to the IC, the IC may be damaged. Please design the IC so that excess current or voltage will not be applied to the IC.

Utmost care is necessary in the design of the output line, VCC and GND line since IC may be destroyed due to short-circuit between outputs, air contamination fault, or fault by improper grounding.

PACKAGE DIMENSIONS

DIP20-P-300-2.54A

Unit: mm



Weight: 2.25 g (Typ.)

RESTRICTIONS ON PRODUCT USE

000707EBA

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